REMARKS

The drawings have been objected to because in the Examiner's view the structure corresponding to "a region of no doped impurities" in claim 2 is not shown in the drawings. Applicant respectfully disagrees with the Examiner. The specification states at page 5, lines 17-20 that "The P^- layer is formed in a region keeping off from an edge of the gate 13g (by an offset length OF in Fig. 2). This offset region is an undoped region of an impurity." This offset region, which is located between the channel of the P-type 101 and the P-type impurity region 13d or 13s, is shown in FIG. 2 as a region labeled as "OF." Thus, this drawing objection should be withdrawn.

Claim 2 has been objected to because, in the Examiner's view, "It is not clear what the 'no doped impurities' is disposed between the gate electrode and the P-type impurity region." Applicant assumes that the Examiner meant to say that it is not clear where the region of no doped impurities is located between the gate electrode and the P-type impurity region. Applicant believes that the original expression in claim 2, i.e., between the gate electrode and the P-type impurity region, is sufficiently clear to define the location of the claimed undoped region, based on the disclosures of the specification explained above. However, for the Examiner to understand the claimed location of the undoped region, applicant has amended claim 2 to state that the region of no doped impurities is disposed between the channel of the P-type and the P-type impurity region. Accordingly, the objection to claim 2 should be withdrawn.

Claims 1, 2 and 5 have been rejected under 35 USC 102(e) as anticipated by U.S. Patent No. 6,781,155 (Yamada). Applicant respectfully traverses this rejection.

Claim 1 recites a driving transistor provided for each of the pixels to drive a corresponding electroluminescent element according to a display signal supplied through a corresponding pixel selecting transistor. Claim 1 also states that the driving transistor has a channel of a P type and is of a lightly-doped-drain type, i.e., LDD structure. The Examiner contends that Yamada's pixel selecting transistor 130 corresponds to the claimed pixel selecting transistor and Yamada's driving transistor corresponds to the clamed driving transistor. The

Examiner also contends that the claim limitation that the driving transistor has a channel of a P type and is of a lightly-doped-drain type is disclosed at column 6, line 17, of Yamada. Applicant respectfully disagrees with the Examiner on his second contention.

The cited passage of Yamada states that "The active layer 13 is of a so-called LLD (lightly doped drain) structure." However, Yamada's active layer 13 is a channel of Yamada's pixel selecting transistor 30 and not that of a driving transistor as claimed. See column 6, lines 3-37, of Yamada. In addition, Yamada's active layer 13 is of an N type and not of a P type as claimed. See column 7, lines 47-63, of Yamada.

It is true that Yamada's device includes a driving transistor, TFT 40, which has a P type channel. However, none of the driving transistors 40 of Yamada's three embodiments is of the claimed lightly-doped-drain type. See column 7, line 64 - column 9, line 16, of Yamada. No part of Yamada teaches or suggests that the LDD structure of Yamada's pixel selecting transistor of the N type be incorporated into Yamada's driving transistor of the P type.

The rejection of claims 1, 2 and 5 under 35 USC 102(e) on Yamada should be withdrawn because Yamada does not teach or suggest the claimed LDD structure.

In light of the above, a Notice of Allowance is solicited.

In the event that the transmittal letter is separated from this document and the Patent and Trademark Office determines that an extension and/or other relief is required, applicant petitions

for any required relief including extensions of time and authorizes the Commissioner to charge the cost of such petitions and/or other fees due in connection with the filing of this document to **Deposit Account No. 03-1952**, referencing Docket No. **606402016700**.

Respectfully submitted,

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By: _____

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